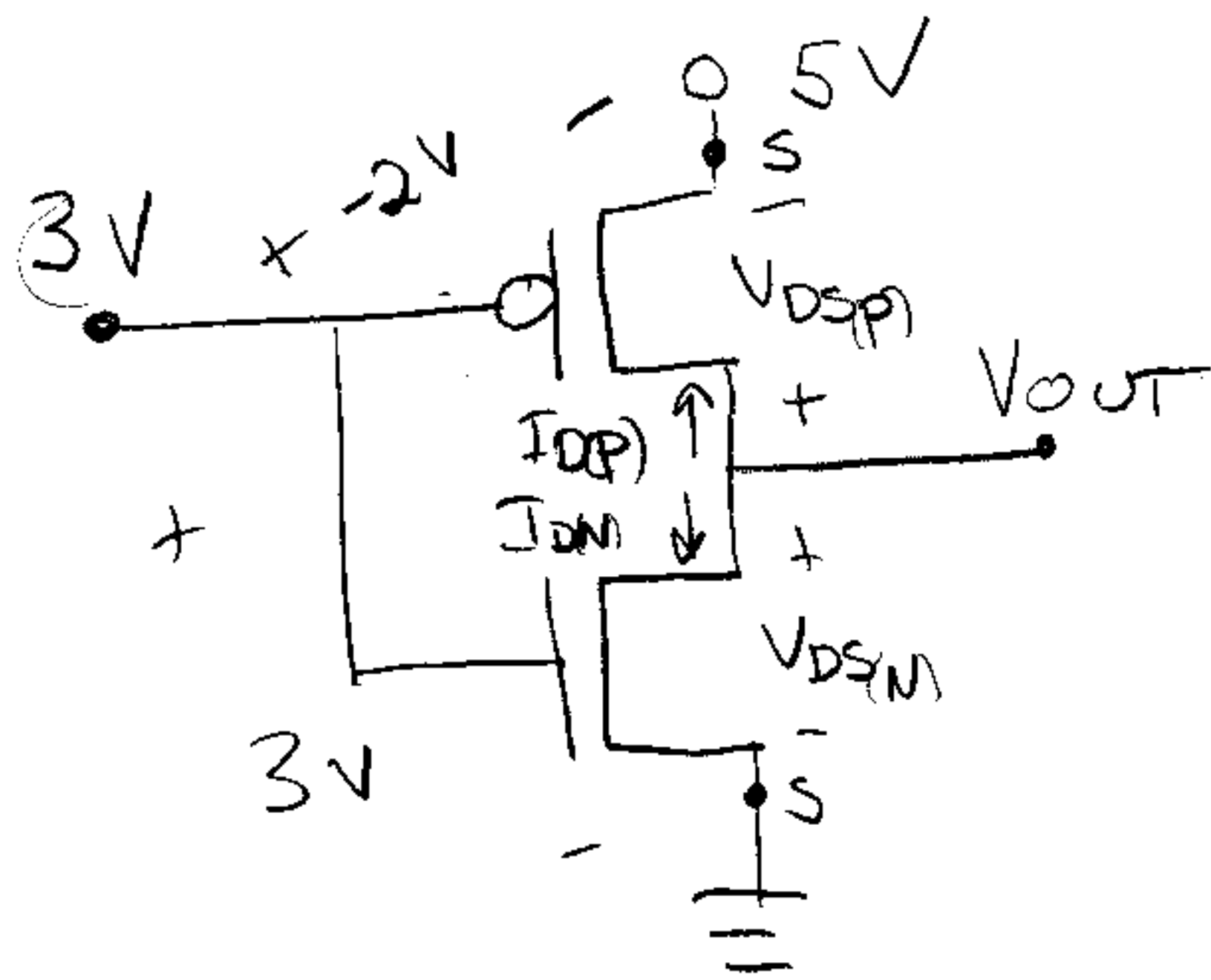


Lecture 22



$$\frac{W}{L} \mu_n C_{ox} = \frac{W}{L} \mu_p C_{ox} = 1 \text{ mA/V}^2$$

$$\lambda_n = \lambda_p = 0 \text{ V}^{-1}$$

$$V_{TH(n)} = 1 \text{ V} \quad V_{TA(p)} = -1 \text{ V}$$

Find V_{out} .

$$-V_{DS(n)} + V_{DS(p)} + 5 \text{ V} = 0$$

$$I_{D(p)} + I_{D(n)} = 0$$

Probably Region D: NMOS triode, PMOS saturation

$$I_{D(p)} = -1 \text{ mA/V}^2 \cdot \frac{1}{2} \cdot (-2 \text{ V} - (-1 \text{ V}))^2 = -\frac{1}{2} \text{ mA}$$

$$I_{D(n)} = 1 \text{ mA/V}^2 \cdot \left(3 \text{ V} - 1 \text{ V} - \frac{V_{DS(n)}}{2} \right) V_{DS(n)}$$

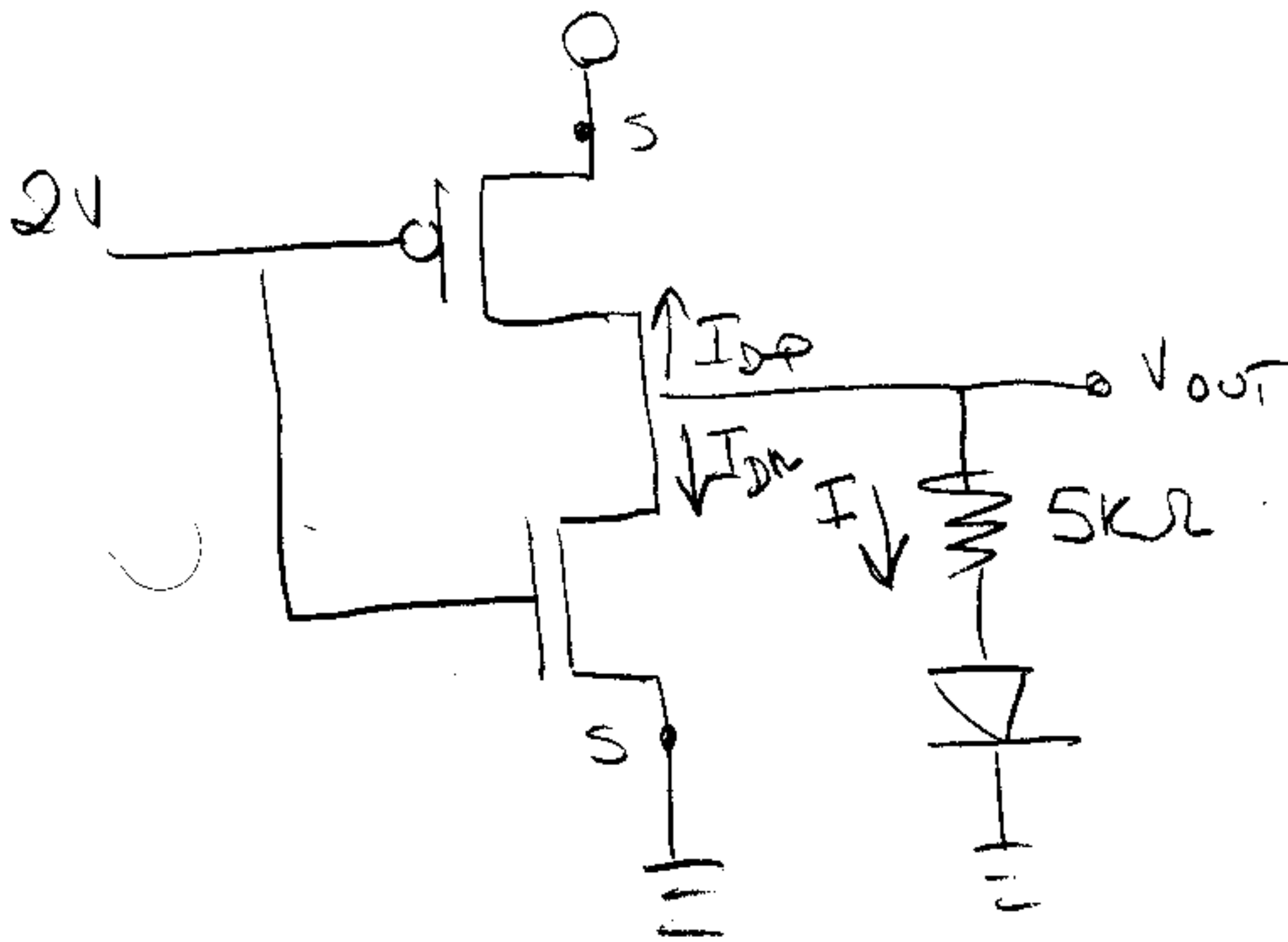
$$= -I_{D(p)} = \frac{1}{2} \text{ mA}$$

$$V_{DS(n)} = \{ 0.27, 3.733 \} \quad 0.27 \text{ V OK for triode}$$

$$V_{DS(p)} = V_{DS(n)} - 5 \text{ V} = -4.73 \text{ V OK for saturation}$$

$$V_{out} = 0.27 \text{ V}$$

2



$$V_{GS(n)} = 2V \quad V_{GS(p)} = -3V$$

$$-V_{DS(n)} + V_{DS(p)} + 5V = 0 \quad I_{D(n)} + I_{D(p)} + I = 0$$

$$V_{DS(n)} = 5kI + 2V \quad (\text{in forward bias})$$

Guess NMOS in saturation, PMOS in triode

$$I_{D(p)} = -1mA/\mu^2 \left(-3V - -1V - \frac{V_{DS(p)}}{2} \right) V_{DS(p)}$$

$$I_{D(n)} = 1mA/\mu^2 (2V - 1V)^2 \cdot 1/2 = 1/2 mA$$

$$= -I_{D(p)} - I$$

$$= 1mA/\mu^2 \left(-2V - \frac{V_{DS(p)}}{2} \right) V_{DS(p)} - \frac{V_{DS(n)} - 2}{5k\Omega}$$

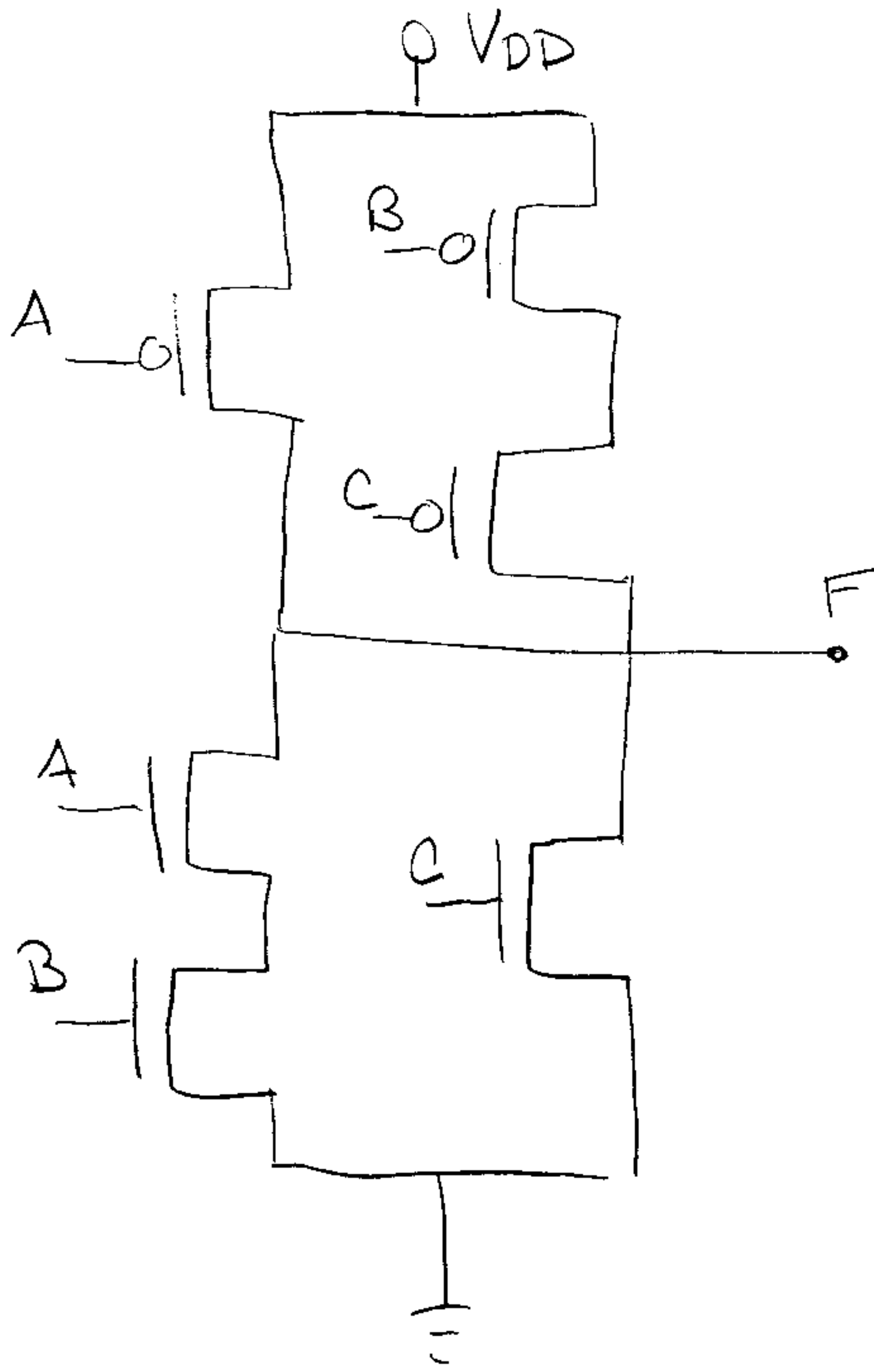
$$= 1mA/\mu^2 \left(-2V - \frac{V_{DS(p)}}{2} \right) V_{DS(p)} - \frac{V_{DS(p)} + 3}{5k\Omega}$$

$$V_{DS(p)} = \{-3.82, -0.58\} \quad \text{For triode, need } V_{DS(p)} > \overbrace{V_{GS(p)} - V_{TH(p)}}^{-2V}$$

$$V_{DS(p)} = -0.58V \quad V_{DS(n)} = 4.42V \quad \text{ok for saturation}$$

$$I = 0.484mA \quad \text{ok for forward bias} \quad \underline{V_{OUT} = 4.42V}$$

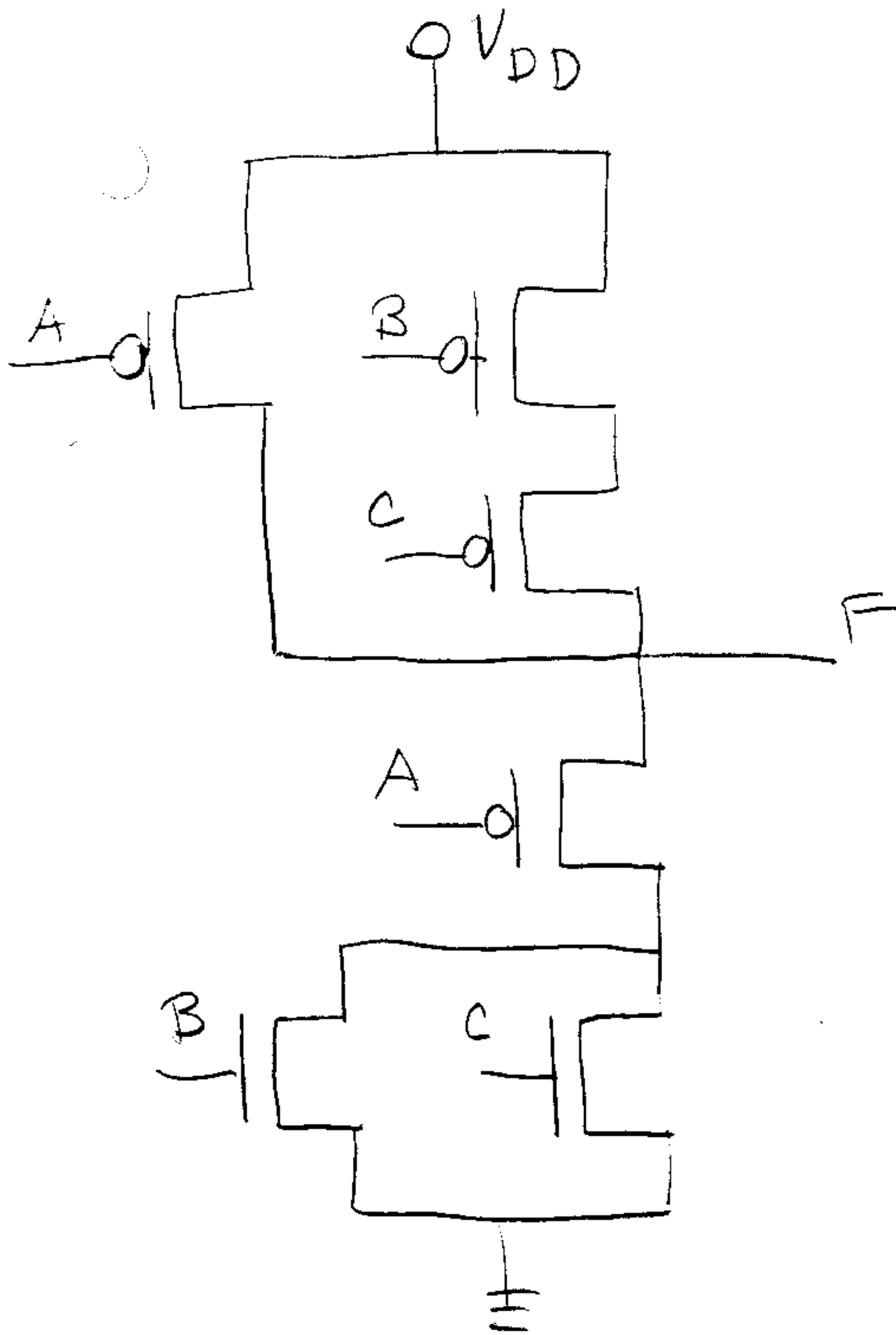
3



Does this circuit perform a logic function?

If so, what function? (Give the Boolean expression).

No — if $A=0$ and $C=1$, then F is simultaneously connected to both V_{DD} & ground.



Does this circuit perform a logic function?
 If so, what function? (write the Boolean expression).

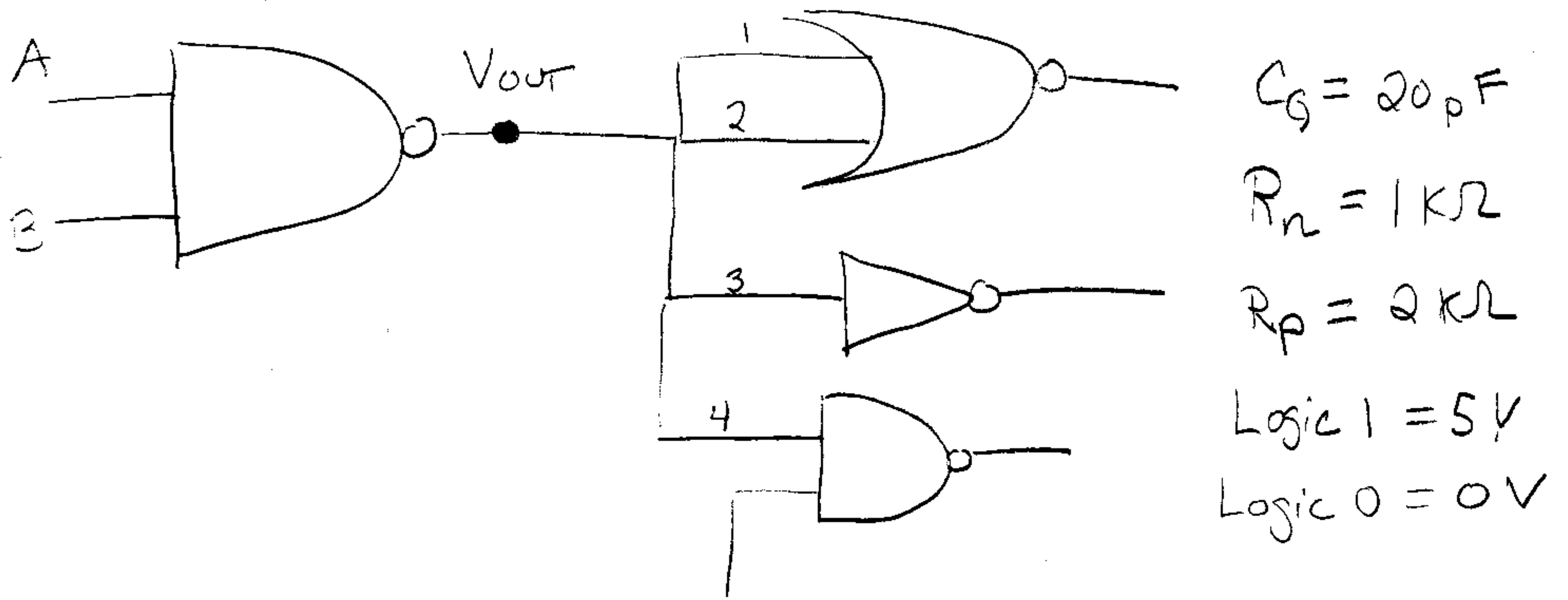
$F = 0$ when $A = 1$ and $(B = 1 \text{ or } C = 1)$

$$\bar{F} = A(B+C) \Rightarrow F = \overline{A(B+C)}$$

Another way to write it:

$F = 1$ when $A = 0$ or $(B = 0 \text{ and } C = 0)$

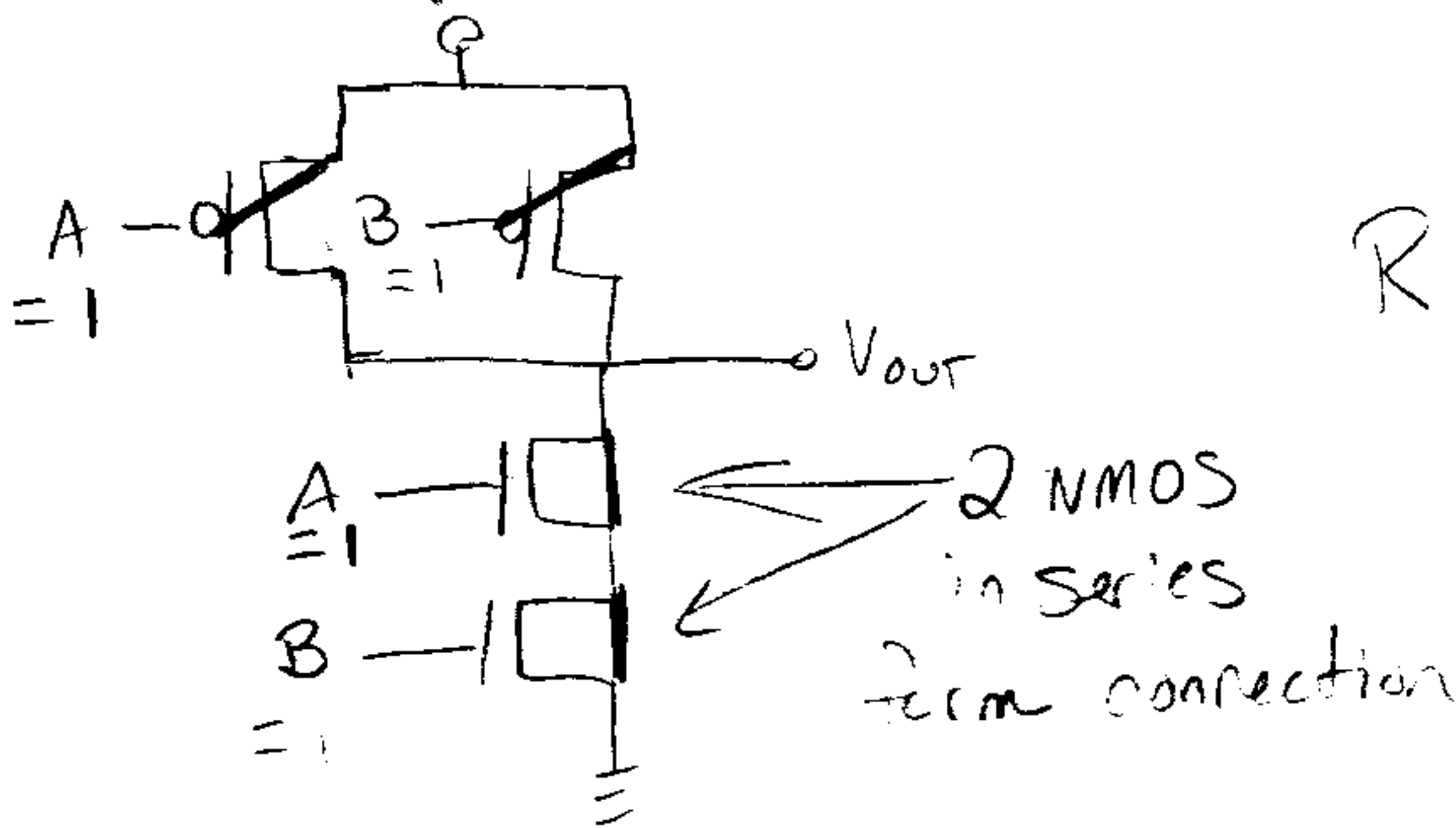
$$F = \bar{A} + \bar{B}\bar{C} \quad \text{Same as above (by DeMorgan).}$$



Suppose that for all $t < 0$, we had $A = 1$ and $B = 0$.
 At $t = 0$, B goes (instantaneously) from 0 to 1.
 Find $V_{out}(t)$ and t_p for the first NAND gate.

V_{out} connected to 4 CMOS inputs.

Each input is 2 transistor gates. $C_g = 4 \times 2 \times 20 \text{ pF} = 160 \text{ pF}$



Before: $A = 1, B = 0 \Rightarrow V_{out} = 5 \text{ V}$ After: $A = 1, B = 1 \Rightarrow V_{out} = 0 \text{ V}$

$$V_{out}(t) = 0 + (5 - 0) e^{-\frac{t}{\tau}} = 5 e^{-\frac{t}{320 \text{ ns}}} \text{ V}$$